

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-60V	125mΩ @ V <sub>GS</sub> = -10V	-4.3A
	190mΩ @ V <sub>GS</sub> = -4.5V	-3.5A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

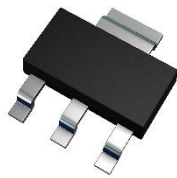
## Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([ZXMP6A17GQ](#))**

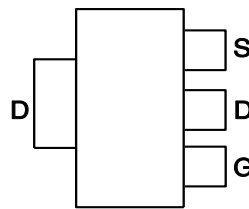
## Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>Ⓔ3</sup>
- Weight: 0.112 grams (Approximate)

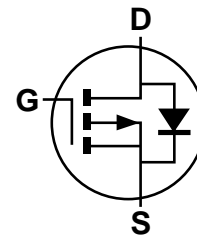
SOT223 (Type DN)



Top View



Pin Out - Top View



Equivalent Circuit

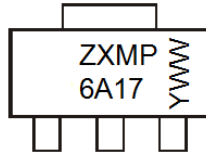
## Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMP6A17GTA	SOT223 (Type DN)	1,000/Tape & Reel
ZXMP6A17GTC	SOT223 (Type DN)	4,000/ Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

SOT223 (Type DN)



ZXMP6A17 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: 1 = 2021)  
 WW or  $\bar{W}W$  = Week (01 to 53)

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

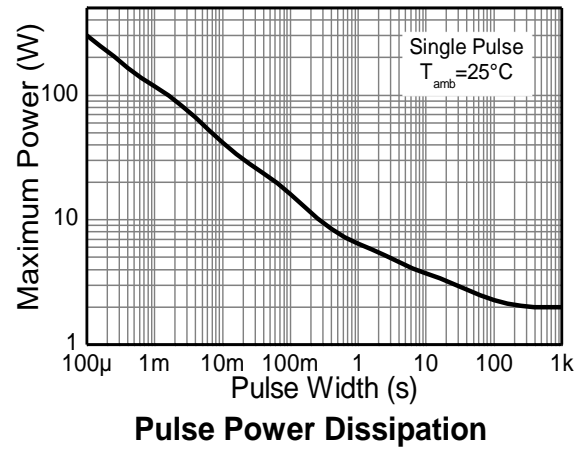
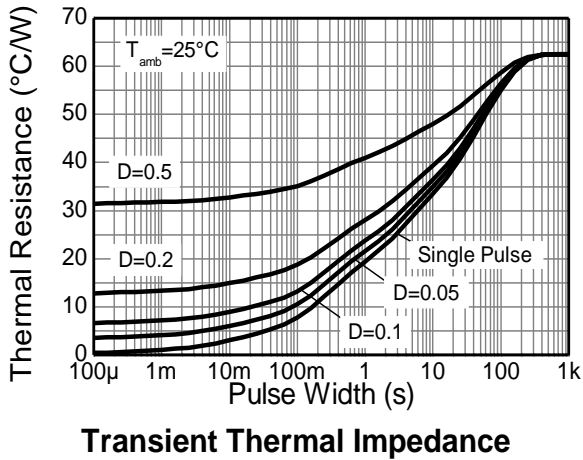
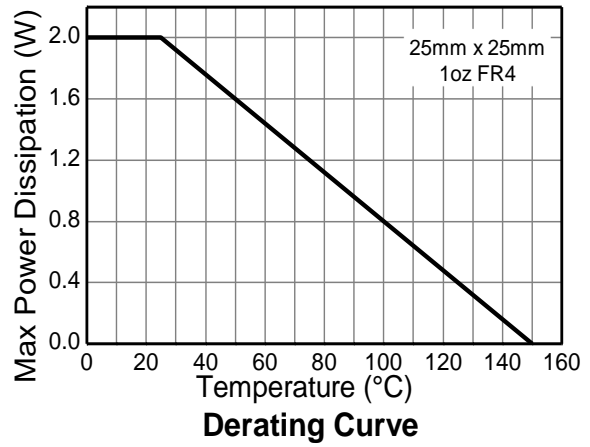
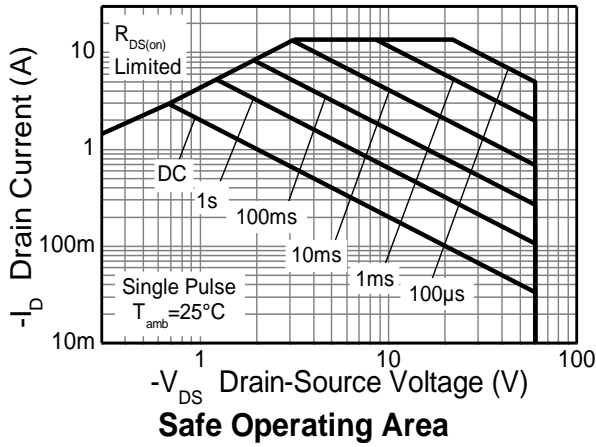
Characteristic			Symbol	Value	Unit	
Drain-Source Voltage			V <sub>DSS</sub>	-60	V	
Gate-Source Voltage			V <sub>GSS</sub>	±20	V	
Continuous Drain Current	V <sub>GS</sub> = 10V	(Note 6)	I <sub>D</sub>	-4.3	A	
		T <sub>A</sub> = +70°C (Note 6)		-3.5		
		(Note 5)		-3.0		
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 7)	I <sub>DM</sub>	-13.7	A	
Continuous Source Current (Body Diode)			(Note 6)	I <sub>S</sub>	-4.3	A
Pulsed Source Current (Body Diode)			(Note 7)	I <sub>SM</sub>	-13.7	A

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	P <sub>D</sub>	2.0	W	
	Linear Derating Factor		(Note 6)		16
Thermal Resistance, Junction to Ambient		(Note 5)	R <sub>θJA</sub>	3.9	mW/°C
	(Note 6)	31			
Thermal Resistance, Junction to Lead	(Note 5)	R <sub>θJA</sub>	62.5	°C/W	
	(Note 6)		32.0		
Thermal Resistance, Junction to Lead		(Note 8)	R <sub>θJL</sub>	9.8	°C/W
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
- For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as Note 5, except the device is measured at t ≤ 10sec.
  - Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
  - Thermal resistance from junction to solder-point (at the end of the drain lead).

**Thermal Characteristics**

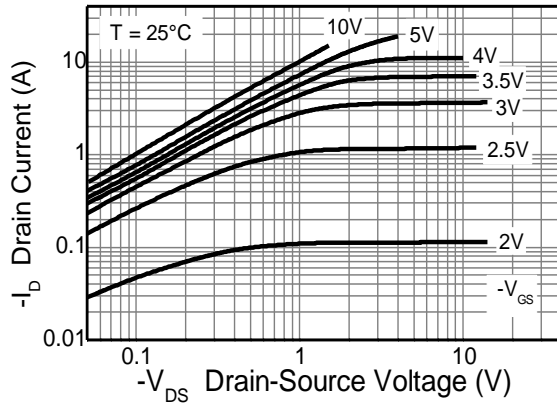


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

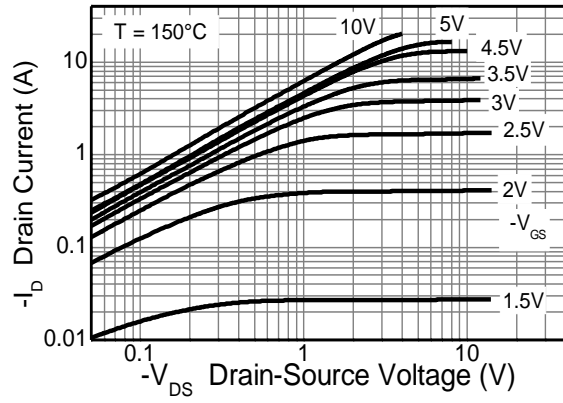
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-0.5	μA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—	—	V	I <sub>D</sub> = -250μA, V <sub>DS</sub> = V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 9)	R <sub>DS(ON)</sub>	—	96	125	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.2A
			120	190		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.8A
Forward Transconductance (Notes 9 & 10)	g <sub>fs</sub>	—	4.7	—	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -2.2A
Diode Forward Voltage (Note 9)	V <sub>SD</sub>	—	-0.85	-0.95	V	I <sub>S</sub> = -2.0A, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	—	25.1	—	ns	I <sub>S</sub> = -1.7A, di/dt = 100A/μs, T <sub>J</sub> = +25°C
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	—	27.2	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iss</sub>	—	637	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	70.0	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	53.0	—	pF	
Total Gate Charge (Note 11)	Q <sub>g</sub>	—	9.0	—	nC	V <sub>GS</sub> = -4.5V
Total Gate Charge (Note 11)	Q <sub>g</sub>	—	17.7	—	nC	V <sub>GS</sub> = -10V V <sub>DS</sub> = -30V I <sub>D</sub> = -2.2A
Gate-Source Charge (Note 11)	Q <sub>gs</sub>	—	1.6	—	nC	
Gate-Drain Charge (Note 11)	Q <sub>gd</sub>	—	4.4	—	nC	
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>	—	2.6	—	ns	V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V I <sub>D</sub> = -1A, R <sub>G</sub> ≅ 6.0Ω
Turn-On Rise Time (Note 11)	t <sub>r</sub>	—	3.4	—	ns	
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>	—	26.2	—	ns	
Turn-Off Fall Time (Note 11)	t <sub>f</sub>	—	11.3	—	ns	

- Notes:
9. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.
  10. For design aid only, not subject to production testing.
  11. Switching characteristics are independent of operating junction temperatures.

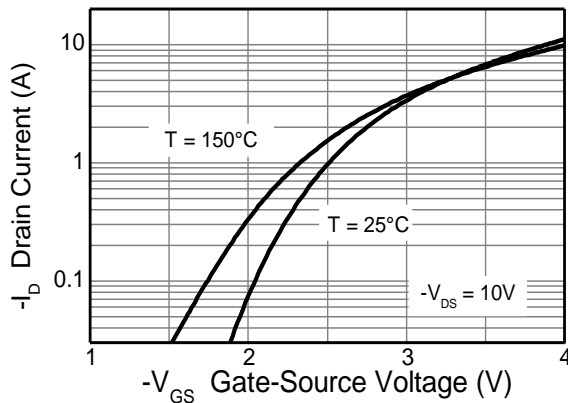
**Typical Characteristics**



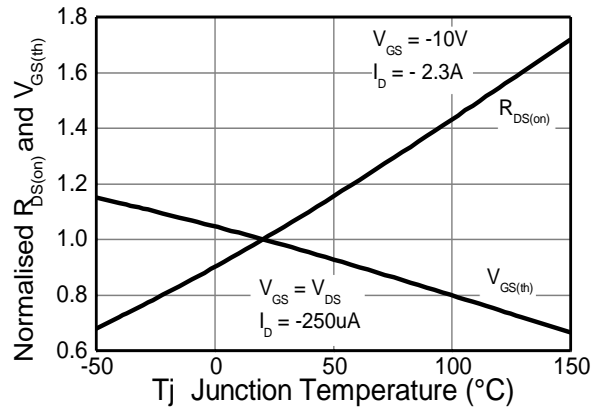
**Output Characteristics**



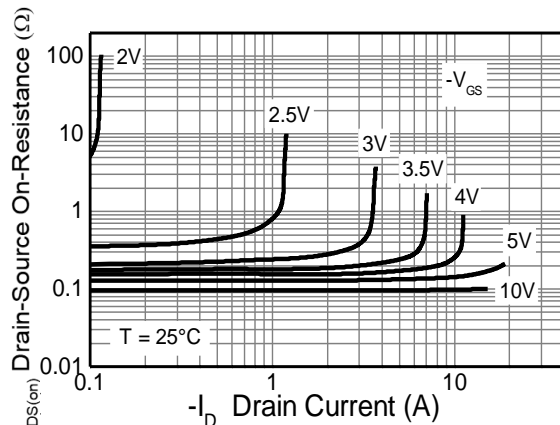
**Output Characteristics**



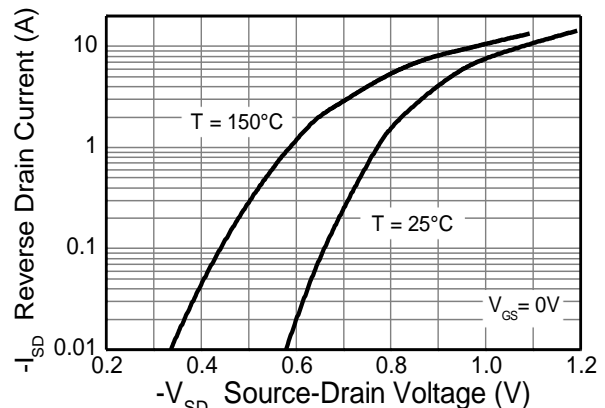
**Typical Transfer Characteristics**



**Normalised Curves v Temperature**

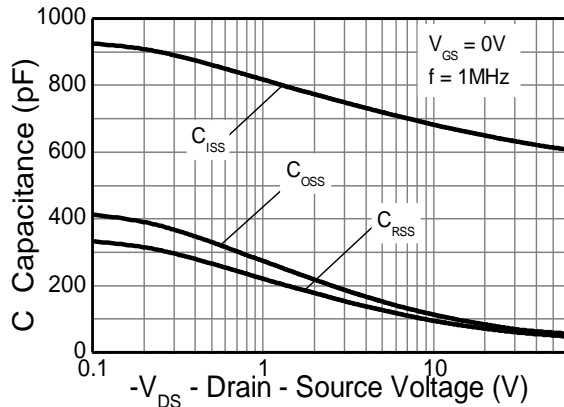


**On-Resistance v Drain Current**

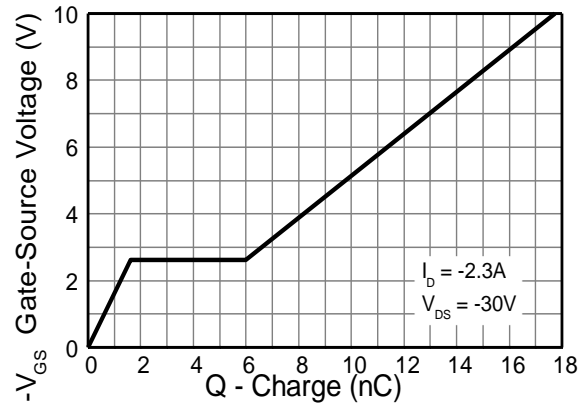


**Source-Drain Diode Forward Voltage**

**Typical Characteristics** (continued)

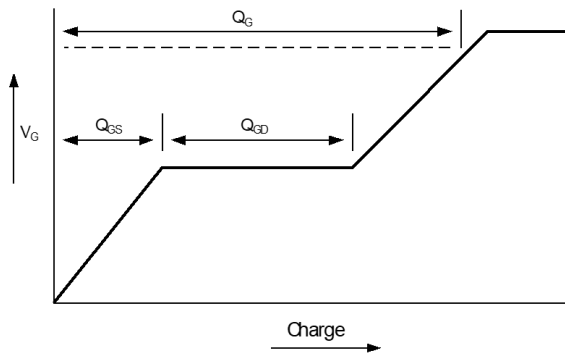


**Capacitance v Drain-Source Voltage**

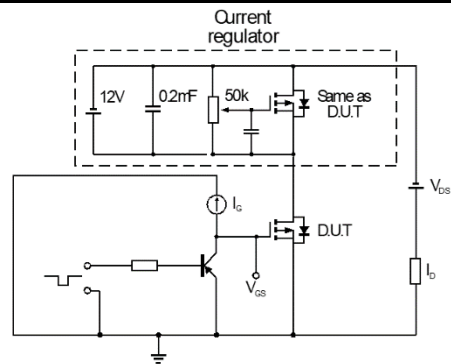


**Gate-Source Voltage v Gate Charge**

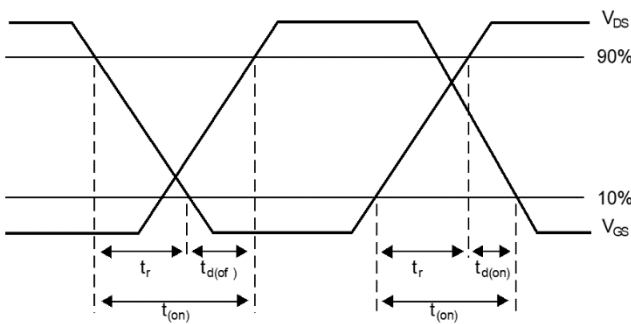
**Test Circuits**



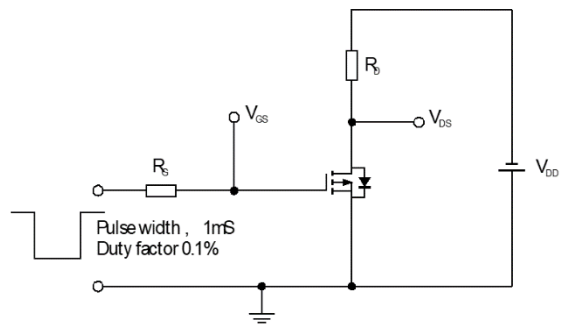
**Basic gate charge waveform**



**Gate charge test circuit**



**Switching time waveforms**

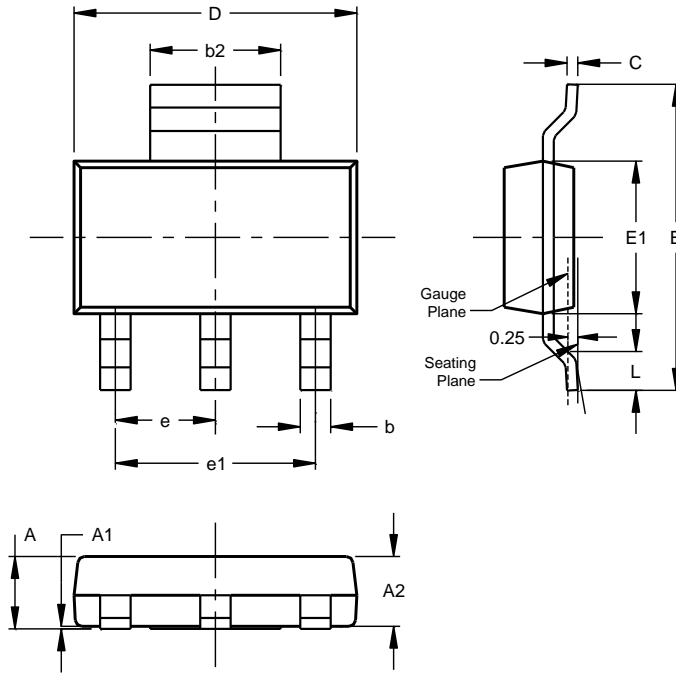


**Switching time test circuit**

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)

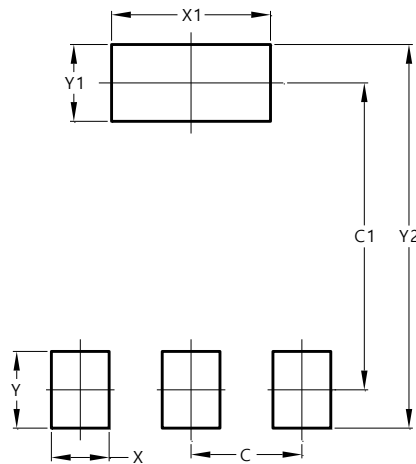


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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